Monday, April 18, TUTORIALS • 8 a.m. — 5:00 p.m.

200. Ultra-thin Dielectrics	220. Memories	240. SER	260. Beyond CMOS
201. Ultra-thin Oxide Reliability E. Wu (IBM) / J. Suñé (U. Autónoma. de Barcelona) (8:00–9:30 a.m.)	221. FLASH: NOR Reliability A. Spinelli (Politecnico di Milano) (8:00–9:30 a.m.)	241. SER: From Fundamentals to Testing and Design R. Baumann (TI) (8:00–11:30 a.m.)	261. Reinventing CMOS T. Dellin (Quick Start Micro Training) (8:00–11:30 a.m.)
202. Breakdown in Devices and Circuits B. Kaczer (IMEC) (10:00 – 11:30 a.m.)	222. FLASH: NAND Reliability R. Shirota (Toshiba) (10:00 – 11:00 a.m.)		
210. NBTI	223. DRAM Reliability C. Mouli (Micron) (1:30 – 3:00 p.m.)	**250. Cu/Low- k Dielectrics**	262. Directions in Nanoelec. H. Hosack/J. Hutchby (SRC) (1:30 – 2:30 p.m.)
211. NBTI: Modeling A. Alam (Purdue) (1:30 – 2:30 p.m.)	**230. High k Dielectrics**	251. Electromigration Reliability in Cu/Low-k P. Ho (UT) (1:30 – 3:00 p.m.)	
212. NBTI: Process, Device, and Circuit A. Krishnan (TI) (3:30 – 5:00 p.m.)	231. High-k Gate Diel.: Characterization G. Bersuker (SEMATECH) (3:30 – 5:00 p.m.)	252. Reliability Issues in Advanced Cu/Low-k Hazara Rathore and Du Nquyen (IBM) (3:30 – 5:00 p.m.)	263. Molecular Electronics C. Richter (NIST) D. Stewart (HP) (3:30 – 5:00 p.m.)